

ULTRA THIN, SINGLE PHASE, DIFFUSION BARRIER FOR METAL CONDUCTORS

Abstract of the Disclosure

The present invention is directed to an alpha-W layer which is employed in interconnect structures such as trench capacitors or damascene wiring levels as a diffusion barrier layer. The alpha-W layer is a single phased material that is formed by a low temperature/pressure chemical vapor deposition process using tungsten hexacarbonyl, $W(CO)_6$, as the source material.

FIG. 2

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